

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A multi-domain liquid crystal display device, comprising:
first and second substrates;
gate and data lines arranged to cross with each other on the first substrate to define a pixel region;
a liquid crystal layer between the first and second substrates;
first and second alignment layers having opposite rubbing directions on the first and second substrates for causing liquid crystal molecules in the liquid crystal layer to form at least two domains having different liquid crystal alignment directions in the pixel; and
at least two electric field distorting means on a domain boundary of the pixel ~~and overlapping the at least two domains~~;
wherein the two electric field distorting means extend to edges of the pixel region ~~are located at an edge area and a central portion of the pixel~~.
2. (Original) The device of claim 1, wherein the electric field distorting means comprises at least one slit.
3. (Original) The device of claim 1, wherein the electric field distorting means comprises a protrusion.
4. (Original) The device of claim 3, wherein the protrusion has a linear shape on the boundary of the two domains.
5. (Previously Presented) The device of claim 1, wherein the electric field distorting means is formed on one of the first and second substrates.
6. (Original) The device of claim 1, wherein a thin film transistor and a pixel electrode are formed on the first substrate.
7. (Original) The device of claim 6, wherein the thin film transistor comprising:
a gate electrode;
a gate insulating layer on the gate electrode;

a semiconductor layer on the gate insulating layer; and
source/drain electrodes on the semiconductor layer.

8. (Original) The device of claim 1, wherein a color filter, a black matrix, and a common electrode are formed on the second substrate.

9. (Original) The device of claim 8, wherein the black matrix is formed on the boundary of the two domains.

10. (Currently Amended) A multi-domain liquid crystal display device, comprising:
first and second substrates;
gate and data lines arranged to cross with each other on the first substrate to define a pixel region;

a pixel electrode on one of the first and second substrates;

a common electrode on another of the first and second substrates;

a liquid crystal layer between the first and second substrates.

first and second alignment layers having opposite rubbing directions on the first and second substrates for causing liquid crystal molecules in the liquid crystal layer to form at least two domains, each domain having different liquid crystal alignment directions in the pixel; and

at least two electric field distorting means on a domain boundary of the pixel ~~and overlapping the two domains~~ on one of the first and second substrates, the electric field distorting means being parallel to the boundary between the two domains such that a linear disclination is formed at the boundary between the two domains when a vertical electric field is formed between the common electrode and the pixel electrode,

wherein the two electric field distorting means extend to edges of the pixel region ~~are located at an edge area and a central portion of the pixel.~~

11. (Original) The device of claim 10, wherein the electric field distorting means is formed at the pixel electrode.

12. (Original) The device of claim 10, wherein the electric field distorting means is formed at the common electrode.

13. (Original) The device of claim 10, wherein the electric field distorting means comprises at least one slit.
14. (Original) The device of claim 10, wherein the electric field distorting means comprises a protrusion.
15. (Original) The device of claim 14, wherein the protrusion has a linear shape on the boundary of the domains.
16. (Previously Presented) The device of claim 10, wherein the electric field distorting means is formed on one of the first and second substrates.
17. (Original) The device of claim 10, wherein a thin film transistor is formed on the same substrate as the pixel electrode.
18. (Original) The device of claim 15, wherein the thin film transistor comprising:
 - a gate electrode;
 - a gate insulating layer on the gate electrode;
 - a semiconductor layer on the gate insulating layer; and
 - source/drain electrodes on the semiconductor layer.
19. (Original) The device of claim 10, wherein a color filter, a black matrix, and a common electrode are formed on the second substrate.
20. (Original) The device of claim 19, wherein the black matrix is formed on the boundary of the domains.